Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A



| PRODUCT SUMMARY | | | | | | | | |
|----------------------------------|------------------|--|--|--|--|--|--|--|
| Package | D-PAK (TO-252AA) | | | | | | | |
| I _{F(AV)} | 8 A | | | | | | | |
| V _R | 600 V | | | | | | | |
| V _F at I _F | 1.7 V | | | | | | | |
| t _{rr} typ. | 18 ns | | | | | | | |
| T _J max. | 150 °C | | | | | | | |
| Diode variation | Single die | | | | | | | |

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Guaranteed avalanche
- Specified at operating conditions
- Compliant to RoHS Directive 2002/95/EC
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | | | |
|--|-----------------------------------|-------------------------|---------------|-------|--|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | | | |
| Cathode to anode voltage | V _{RRM} | | 600 | V | | | | | |
| Maximum continuous forward current | I _F | T _C = 100 °C | 8 | | | | | | |
| Single pulse forward current | I _{FSM} | | 60 | А | | | | | |
| Peak repetitive forward current | I _{FRM} | | 24 | | | | | | |
| Maximum power dissipation | PD | T _C = 100 °C | 14 | W | | | | | |
| Operating junction and storage temperature range | T _J , T _{Stg} | | - 55 to + 150 | °C | | | | | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified) | | | | | | | | | |
|--|-------------------------------------|--|-------------|------|------|------|-------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS | | |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 600 | - | - | | | | |
| Forward voltage | | I _F = 8 A | | - | 1.4 | 1.7 | v | | |
| | V _F | I _F = 16 A | See fig. 1 | - | 1.7 | 2.1 | - | | |
| | | I _F = 8 A, T _J = 125 °C | | - | 1.4 | 1.7 | | | |
| Maximum reverse | | $V_R = V_R$ rated | - | 0.3 | 5.0 | μA | | | |
| leakage current | I _R | $T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$ | - | 100 | 500 | | | | |
| Junction capacitance | CT | V _R = 200 V See fig. 3 | | - | 10 | 25 | pF | | |
| Series inductance | Ls | Measured lead to lead 5 mm from pa | ackage body | - | 8.0 | - | nH | | |

Revision: 14-Jun-11

Document Number: 94042

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

1





VS-HFA08SD60SPbF

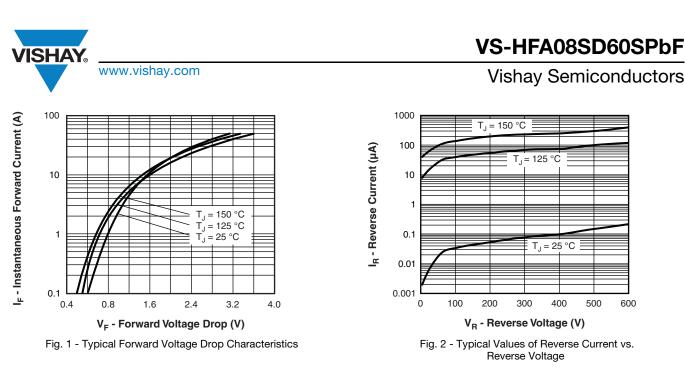


www.vishay.com

Vishay Semiconductors

| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified) | | | | | | | | | |
|---|--------------------------|---|--|------|------|------|------------|--|--|
| PARAMETER | SYMBOL | TEST CO | NDITIONS | MIN. | TYP. | MAX. | UNITS | | |
| Reverse recovery time | | $I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$ | - | 18 | - | | | | |
| | t _{rr} | T _J = 25 °C | | - | 37 | 55 | ns | | |
| | | T _J = 125 °C | | - | 55 | 90 | | | |
| Deale receiver a surrent | I _{RRM} | T _J = 25 °C | I _F = 8 A dI _F /dt = 200 A/μs V _R = 200 V | - | 3.5 | 5.0 | A | | |
| Peak recovery current | | T _J = 125 °C | | - | 4.5 | 8.0 | | | |
| Boyoroo roooyory oborgo | Q _{rr} | T _J = 25 °C | | - | 65 | 138 | nC A/µs | | |
| Reverse recovery charge | | T _J = 125 °C | | - | 124 | 360 | | | |
| Rate of fall of recovery current | dl _{(rec)M} /dt | T _J = 25 °C | | - | 240 | - | | | |
| hate of fail of recovery current | | T _J = 125 °C | | - | 210 | - | | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | | |
|---|-----------------------------------|----------------------|------|-------|-------|-------|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | | |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | - 55 | - | 150 | °C | | | |
| Thermal resistance, junction to case | R _{thJC} | | - | - | 3.5 | °C/W | | | |
| Thermal resistance, junction to ambient | R _{thJA} | Typical socket mount | - | - | 80 | C/W | | | |
| Weight | | | - | 2.0 | - | g | | | |
| weight | | | - | 0.07 | - | oz. | | | |
| Marking device | | Case style D-PAK | | HFA08 | SD60S | | | | |



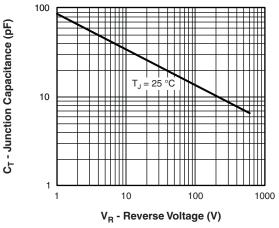


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

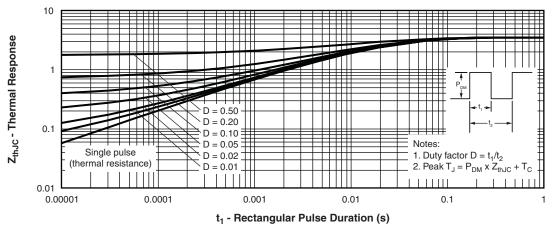


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

3



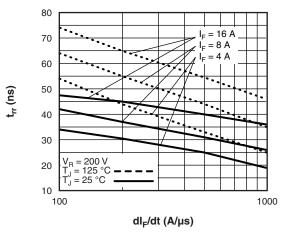


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

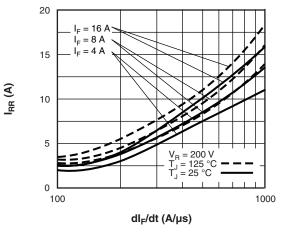
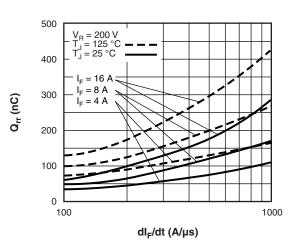


Fig. 6 - Typical Recovery Current vs. dl_F/dt

VS-HFA08SD60SPbF

Vishay Semiconductors





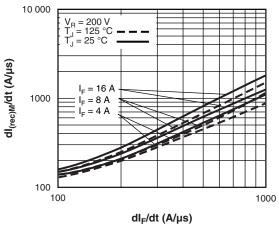


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

Revision: 14-Jun-11 **4** Document Number: 94042 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

VS-HFA08SD60SPbF



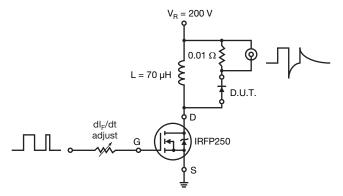
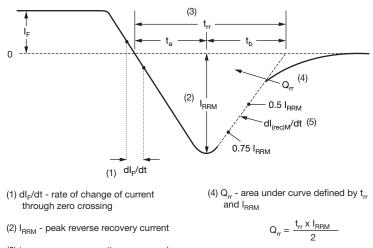


Fig. 9 - Reverse Recovery Parameter Test Circuit



(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

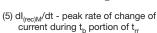


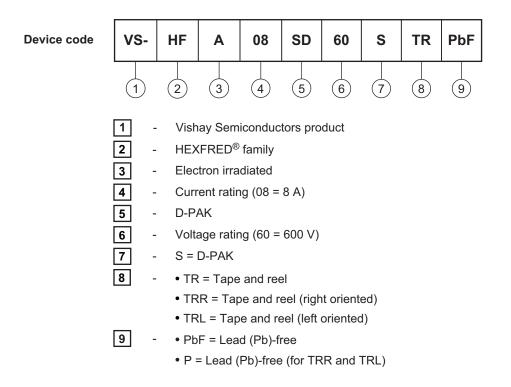
Fig. 10 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors



ORDERING INFORMATION TABLE



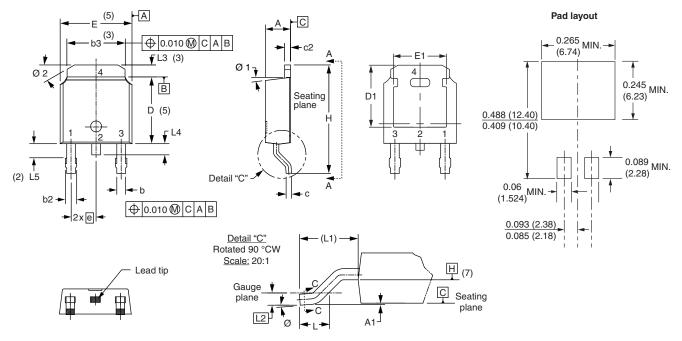
| LINKS TO RELATED DOCUMENTS | | | | | | | | |
|----------------------------|--------------------------|--|--|--|--|--|--|--|
| Dimensions | www.vishay.com/doc?95016 | | | | | | | |
| Part marking information | www.vishay.com/doc?95059 | | | | | | | |
| Packaging information | www.vishay.com/doc?95033 | | | | | | | |



Vishay Semiconductors

D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



| SYMBOL | MILLIN | IETERS | INC | HES | NOTES | | SYMBOL | MILLIN | IETERS | INC | HES | NOTES |
|----------|--------|--------|-------|-------|-------|-------|----------|--------|--------|-------|-------|-------|
| STINIBUL | MIN. | MAX. | MIN. | MAX. | NOTES | NOTES | STIVIDUL | MIN. | MAX. | MIN. | MAX. | NUTES |
| А | 2.18 | 2.39 | 0.086 | 0.094 | | | е | 2.29 | BSC | 0.090 |) BSC | |
| A1 | - | 0.13 | - | 0.005 | | | Н | 9.40 | 10.41 | 0.370 | 0.410 | |
| b | 0.64 | 0.89 | 0.025 | 0.035 | | | L | 1.40 | 1.78 | 0.055 | 0.070 | |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 | | | L1 | 2.74 | BSC | 0.108 | BREF. | |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 | 3 | | L2 | 0.51 | BSC | 0.020 | BSC | |
| с | 0.46 | 0.61 | 0.018 | 0.024 | | | L3 | 0.89 | 1.27 | 0.035 | 0.050 | 3 |
| c2 | 0.46 | 0.89 | 0.018 | 0.035 | | | L4 | - | 1.02 | - | 0.040 | |
| D | 5.97 | 6.22 | 0.235 | 0.245 | 5 | | L5 | 1.14 | 1.52 | 0.045 | 0.060 | 2 |
| D1 | 5.21 | - | 0.205 | - | 3 | | Ø | 0° | 10° | 0° | 10° | |
| E | 6.35 | 6.73 | 0.250 | 0.265 | 5 | | Ø1 | 0° | 15° | 0° | 15° | |
| E1 | 4.32 | - | 0.170 | - | 3 | | Ø2 | 25° | 35° | 25° | 35° | |

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

⁽⁴⁾ Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA

Document Number: 95016



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.